[CLAIMS]

[Claim 1]

A component for fabricating an SiC semiconductor having a plurality of layers having different transmittances, the component comprising two or more superposed layers,

wherein each of superposed layers contains SiC and has a transmittance value different from that of another adjacent layer,

wherein a color is gradually changed at a boundary of superposed layers.

[Claim 2]

The component for fabricating an SiC semiconductor of claim 1, wherein compositions of the superposed layers are the same.

[Claim 3]

The component for fabricating an SiC semiconductor of claim 1, wherein the superposed layers are superposed on a graphite base material.

[Claim 4]

The component for fabricating an SiC semiconductor of claim 1, wherein interception of growth of one or more abnormal crystals is included in the boundary of superposed layers.

[Claim 5]

The component for fabricating an SiC semiconductor of claim 1, wherein the component for fabricating a semiconductor is a component of a plasma processing device and includes at least one selected from a group consisting of a ring, an electrode, and a conductor.

[Claim 6]

The component for fabricating an SiC semiconductor of any one of claims 1 to

5, further comprising:

a regenerating unit containing SiC formed on at least a part of the superposed layer.

[Claim 7]

The component for fabricating an SiC semiconductor of claim 6, wherein colors between the regenerating unit containing SiC and a superposed layer adjacent to the regenerating unit are different.

[Claim 8]

A manufacturing method of a component for fabricating an SiC semiconductor of claim 1, the method comprising:

in a chemical vapor deposition chamber including a plurality of raw material gas injecting introduction holes,

superposing a first layer containing SiC using a first introduction hole group including some of the plurality of raw material gas injecting introduction holes; and

superposing a second layer containing SiC using a second introduction hole group including the other some of the plurality of raw material gas injecting introduction holes.

[Claim 9]

The manufacturing method of claim 8, further comprising:

superposing a third layer containing SiC using a third introduction hole group after the superposing of a second layer.

[Claim 10]

The manufacturing method of claim 8, wherein between the superposing of layers, the component for fabricating an SiC semiconductor is maintained in the chemical vapor deposition chamber.

[Claim 11]

The manufacturing method of claim 8, wherein in the chemical vapor deposition chamber, locations of the introduction hole groups are different.

[Claim 12]

The manufacturing method of claim 8, wherein times to perform the superposing of layers are different.

[Claim 13]

A manufacturing method of a component for fabricating an SiC semiconductor, the method comprising:

in a chemical vapor deposition chamber including a plurality of raw material gas injecting introduction holes,

superposing a first layer containing SiC using a first introduction hole group including some of the plurality of raw material gas injecting introduction holes; and

superposing a second layer containing SiC using a second introduction hole group including the other some of the plurality of raw material gas injecting introduction holes,

processing plasma on the component for fabricating an SiC semiconductor in a dry etching device; and

forming a regenerating unit containing SiC on at least a part of the superposed layer of the component for fabricating an SiC semiconductor,

wherein the first layer and the second layer have a different transmittance value,

wherein a color is gradually changed at a boundary between the first layer and the second layer.

[Claim 14]

The manufacturing method of claim 13, wherein an average thickness of the

regenerating unit is 0.1 mm to 3 mm.

[Claim 15]

The manufacturing method of claim 13, further comprising:

between the processing of plasma and the forming of a regenerating unit,

processing the component for fabricating an SiC semiconductor, a pre-cleaning step, or both the processing and the pre-cleaning step.

[Claim 16]

The manufacturing method of claim 13, further comprising:

after the forming of a regenerating unit,

a post-processing step of the formed regenerating unit, a post-cleaning step, or both the steps.